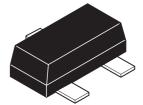


# ZXMP2120FF 200V SOT23F P-channel enhancement mode MOSFET

## **Summary**

V <sub>(BR)DSS</sub>	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (mA)	
-200	28 @ V <sub>GS</sub> = -10V	-137	



## **Description**

This 200V enhancement mode P-channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and freedom from thermal runaway and thermally induced secondary breakdown.

Applications benefiting from this device include a variety of telecom and general high voltage circuits.

#### **Features**

- High voltage
- · Low on-resistance
- · Fast switching speed
- · Low gate drive
- · Low threshold
- SOT23 FLAT package

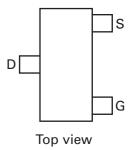
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## **Applications**

Active clamping of primary side MOSFETs in 48 volt DC-DC converters

## **Ordering information**

Device	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXMP2120FFTA	7	8	3,000	



## **Device marking**

1C4

## **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Drain-source voltage	V <sub>DSS</sub>	-200	V
Gate-source voltage	V <sub>GS</sub>	± 20	V
Continuous drain current @ V <sub>GS</sub> = 10V; T <sub>amb</sub> =25°C <sup>(a)</sup>	I <sub>D</sub>	-137	mA
Pulsed drain current <sup>(c)</sup>	I <sub>DM</sub>	-0.8	А
Pulsed source current (body diode)(c)	I <sub>SM</sub>	-0.8	Α
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	1	W
Linear derating factor		8	mW/°C
Power dissapation at T <sub>amb</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.5	W
Linear derating factor		12.3	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	125	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	81	°C/W

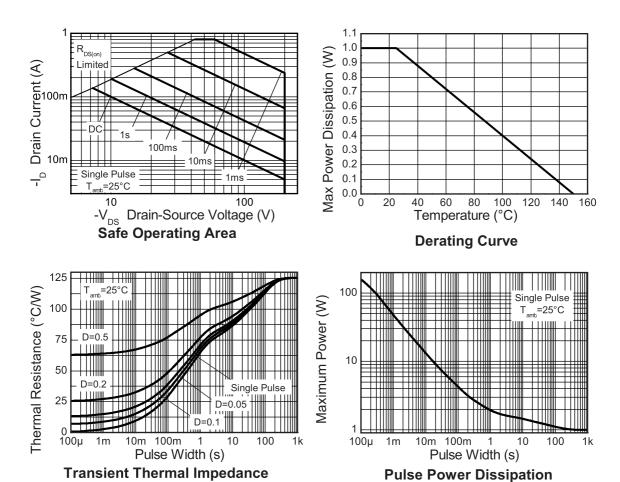
#### NOTES:

<sup>(</sup>a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>b) For a device surface mounted on FR4 pcb measured at  $t \le 5$  sec.

<sup>(</sup>c) Repetitive rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width  $300\mu s$  - pulse width limited by maximum junction temperature.

#### Thermal characteristics



# Electrical characteristics (at T<sub>amb</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Max.	Unit	Conditions		
Static							
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	-200		V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V		
Zero gate voltage drain current	I <sub>DSS</sub>		-10	μΑ	V <sub>DS</sub> = -200V, V <sub>GS</sub> =0V		
			-100	μΑ	$V_{DS}$ = -160V, $V_{GS}$ =0V, T=125C <sup>(‡)</sup>		
Gate-body leakage	I <sub>GSS</sub>		20	nA	$V_{GS}$ =±20V, $V_{DS}$ =0V		
Gate-source threshold voltage	V <sub>GS(th)</sub>	-1.5	-3.5	V	$I_D=250\mu A, V_{DS}=V_{GS}$		
Static drain-source on-state resistance (*)	R <sub>DS(on)</sub>		28	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -150mA		
On-state drain current <sup>(*)</sup>	I <sub>D(on)</sub>	-300		mA	V <sub>DS</sub> = -25V, V <sub>GS</sub> =-10V		
Forward transconductance(*) (‡)	9 <sub>fs</sub>	50		mS	V <sub>DS</sub> = -25V, I <sub>D</sub> = -150mA		
Dynamic <sup>(‡)</sup>							
Input capacitance	C <sub>iss</sub>		100	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> =0V		
Output capacitance	C <sub>oss</sub>		25	pF	f=1MHz		
Reverse transfer capacitance	C <sub>rss</sub>		7	pF			
Switching (†) (‡)							
Turn-on-delay time	t <sub>d(on)</sub>		7	ns	V <sub>DD</sub> = -25V, V <sub>GS</sub> = -10V		
Rise time	t <sub>r</sub>		15	ns	I <sub>D</sub> = -150mA		
Turn-off delay time	t <sub>d(off)</sub>		12	ns	R <sub>SOURCE</sub> ≈ 50Ω		
Fall time	t <sub>f</sub>		15	ns			

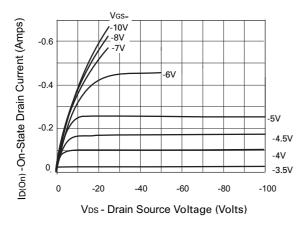
#### NOTES

<sup>(\*)</sup> Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

<sup>(†)</sup> Switching characteristics are independent of operating junction temperature.

<sup>(‡)</sup> For design aid only, not subject to production testing.

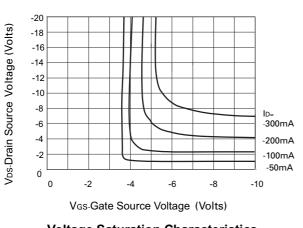
## **Typical charateristics**

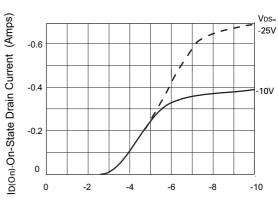


-0.4 -0.4 -0.5 -0.1 -0.1 -0.2 -0.2 -0.1 -0.1 -0.1 -0.2 -0.2 -4 -6 -8 -10 VDs - Drain Source Voltage (Volts)

## **Output Characteristics**

**Saturation Characteristics** 

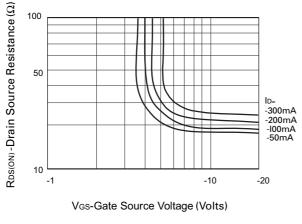


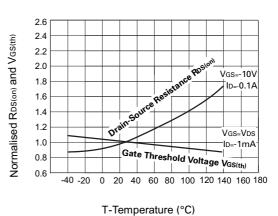


#### **Voltage Saturation Characteristics**

Vgs-Gate Source Voltage (Volts)

Transfer Characteristics

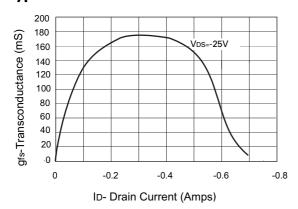




On-resistance vs gate-source voltage

Normalised RDS(on) and VGS(th) vs Temperature

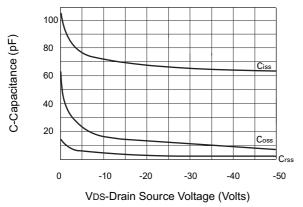
## **Typical characteristics**

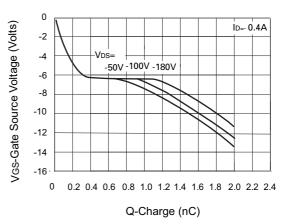


200 180 gfs-Transconductance (mS) 160 140 120 VDS=-25V 100 80 60 40 20 0 0 -2 -6 -8 -10 VGS-Gate Source Voltage (Volts)

#### Transconductance v drain current

Transconductance v gate-source voltage

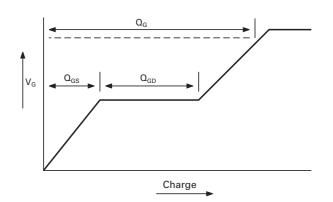




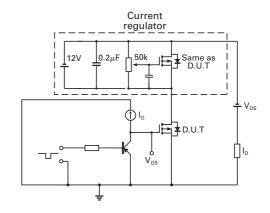
Capacitance v drain-source voltage

Gate charge v gate-source voltage

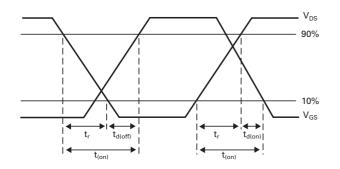
# **Typical characteristics**



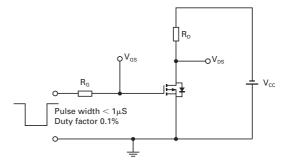
Basic gate charge waveform



Gate charge test circuit



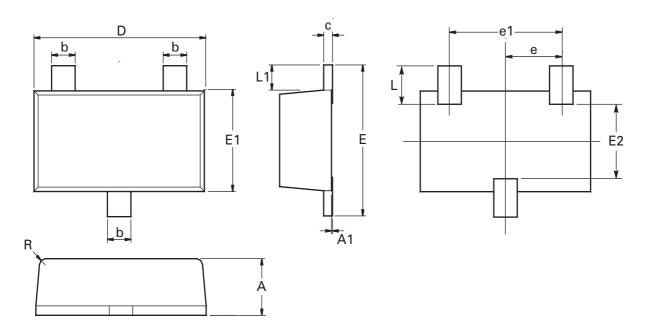
Switching time waveforms



Switching time test circuit

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# Package outline - SOT23F



Dim.	Millim	neters	Inc	hes	Dim.	Millim	eters	Inc	hes
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
Α	0.80	1.00	0.0315	0.0394	Е	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	E2	1.10	1.26	0.0433	0.0496
С	0.10	0.20	0.0043	0.0079	L	0.48	0.68	0.0189	0.0268
D	2.80	3.00	0.1102	0.1181	L1	0.30	0.50	0.0153	0.0161
е	0.95	ref	0.037	74 ref	R	0.05	0.15	0.0019	0.0059
e1	1.80	2.00	0.0709	0.0787	0	0°	12°	0°	12°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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